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BC846, BC847, BC848

General Purpose Transistors

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847 BC848	V_{CEO}	65 45 30	V
Collector-Base Voltage BC846 BC847 BC848	V_{CBO}	80 50 30	V
Emitter-Base Voltage BC846 BC847 BC848	V_{EBO}	6.0 6.0 5.0	V
Collector Current – Continuous	I_C	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

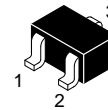
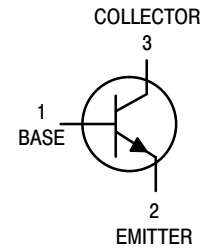
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$	P_D	200	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	620	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.



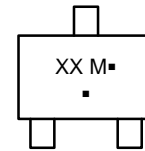
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**SC-70/SOT-323
CASE 419
STYLE 3**

MARKING DIAGRAM



XX = Specific Device Code
M = Month Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 12 of this data sheet.

BC846, BC847, BC848

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit	
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I _C = 10 mA)	BC846 Series BC847 Series BC848 Series	V _{(BR)CEO}	65 45 30	– – –	– – –	V
Collector–Emitter Breakdown Voltage (I _C = 10 μA, V _{EB} = 0)	BC846 Series BC847 Series BC848 Series	V _{(BR)CES}	80 50 30	– – –	– – –	V
Collector–Base Breakdown Voltage (I _C = 10 μA)	BC846 Series BC847 Series BC848 Series	V _{(BR)CBO}	80 50 30	– – –	– – –	V
Emitter–Base Breakdown Voltage (I _E = 1.0 μA)	BC846 Series BC847 Series BC848 Series	V _{(BR)EBO}	6.0 6.0 5.0	– – –	– – –	V
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)		I _{CBO}	– –	– –	15 5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V) (I _C = 2.0 mA, V _{CE} = 5.0 V)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	h _{FE}	– – –	90 150 270	– – –	– – –
Collector–Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)		V _{CE(sat)}	– –	– –	0.25 0.6	V
Base–Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)		V _{BE(sat)}	– –	0.7 0.9	– –	V
Base–Emitter Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)		V _{BE(on)}	580 –	660 –	700 770	mV
SMALL–SIGNAL CHARACTERISTICS						
Current–Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	100	–	–	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)		C _{obo}	–	–	4.5	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	–	–	10	dB

BC846, BC847, BC848

BC846A, BC847A, BC848A

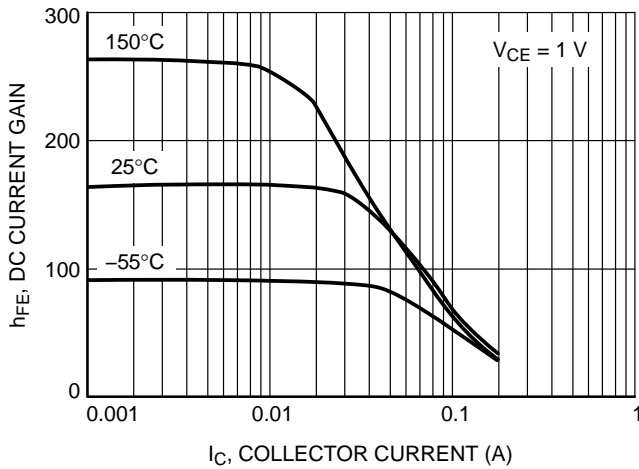


Figure 1. DC Current Gain vs. Collector Current

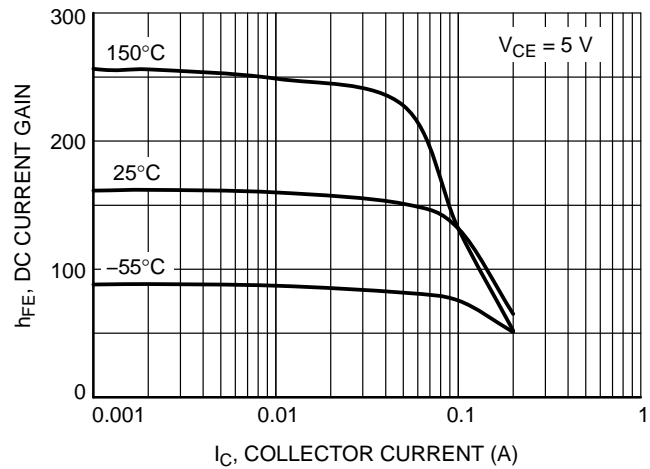


Figure 2. DC Current Gain vs. Collector Current

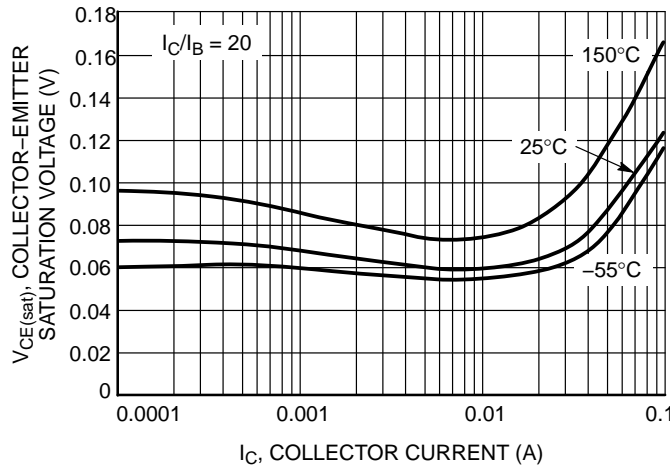


Figure 3. Collector-Emitter Saturation Voltage vs. Collector Current

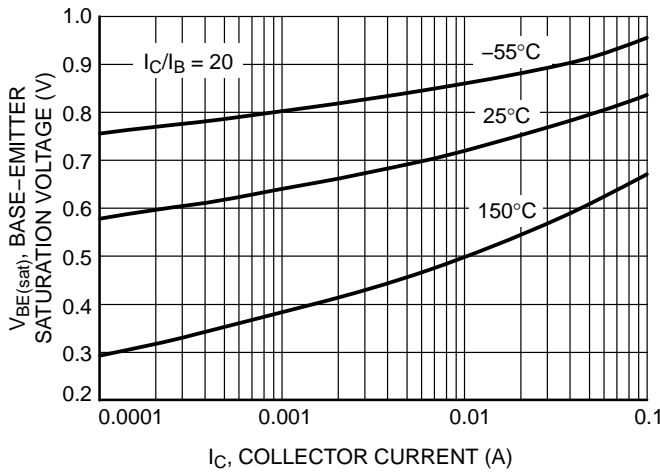


Figure 4. Base-Emitter Saturation Voltage vs. Collector Current

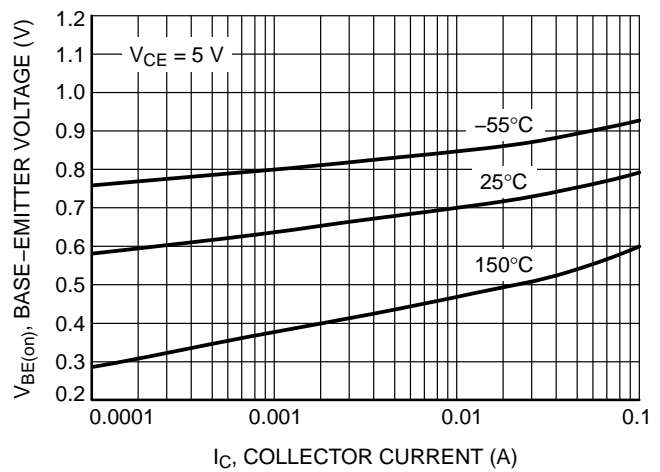


Figure 5. Base-Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC846A, BC847A, BC848A

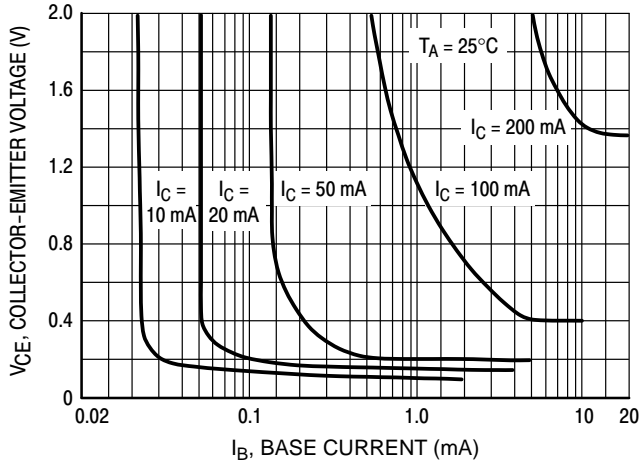


Figure 6. Collector Saturation Region

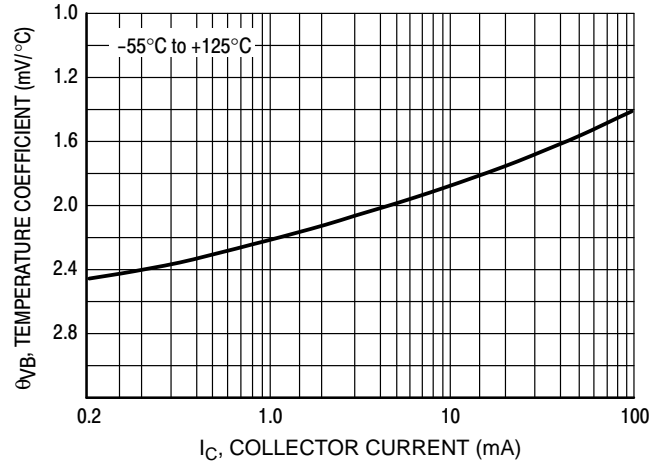


Figure 7. Base-Emitter Temperature Coefficient

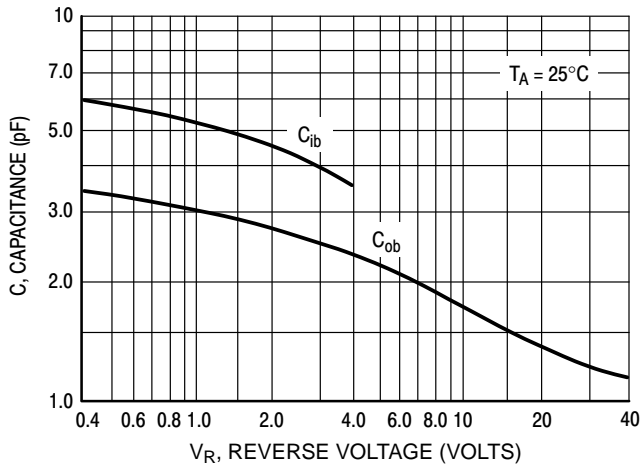


Figure 8. Capacitances

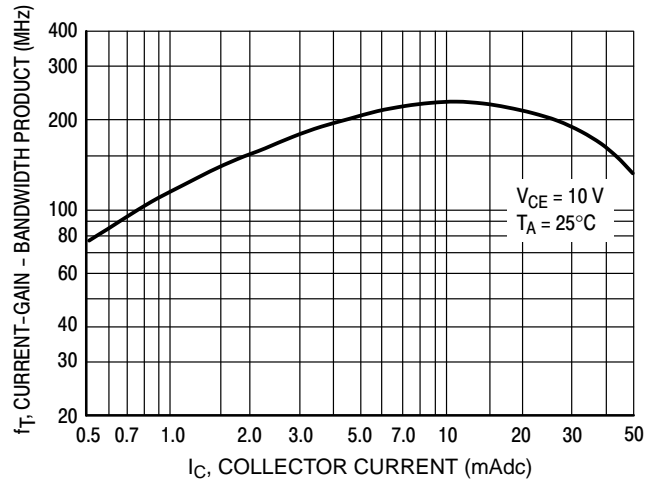


Figure 9. Current-Gain - Bandwidth Product

BC846, BC847, BC848

BC846B

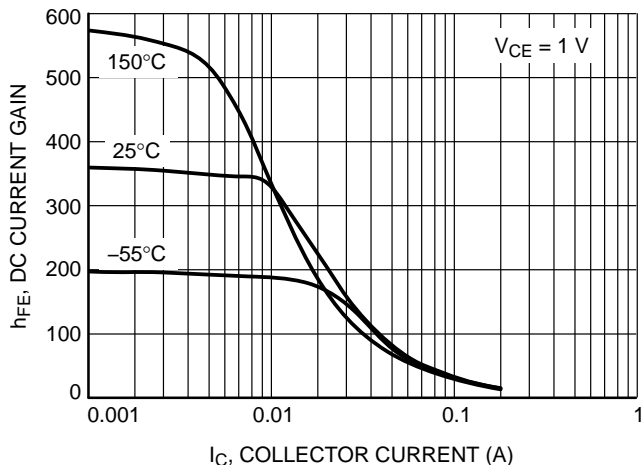


Figure 10. DC Current Gain vs. Collector Current

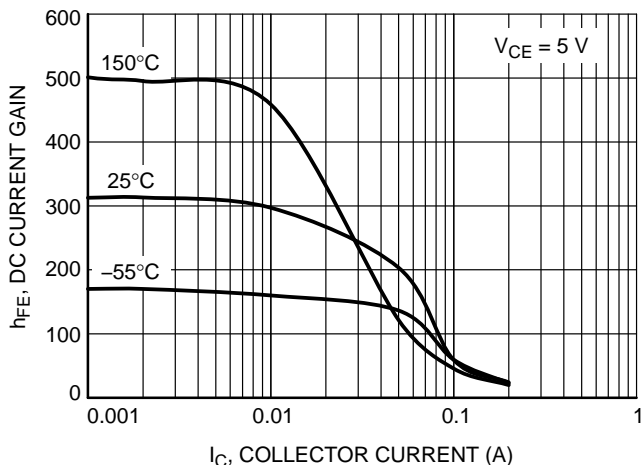


Figure 11. DC Current Gain vs. Collector Current

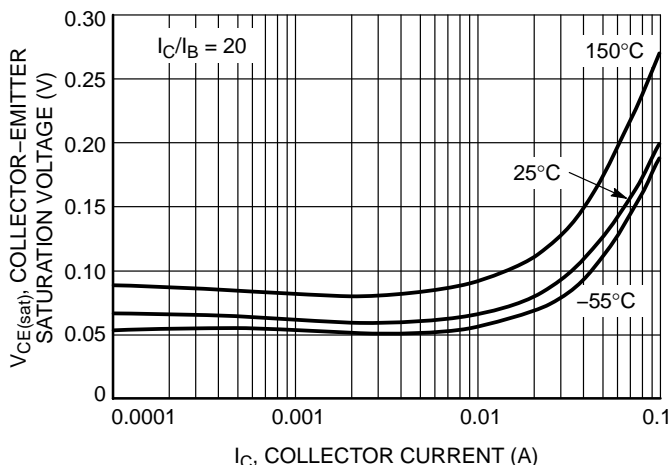


Figure 12. Collector Emitter Saturation Voltage vs. Collector Current

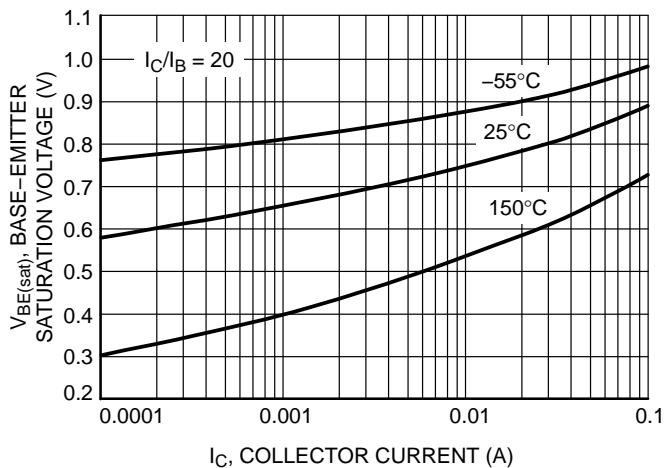


Figure 13. Base Emitter Saturation Voltage vs. Collector Current

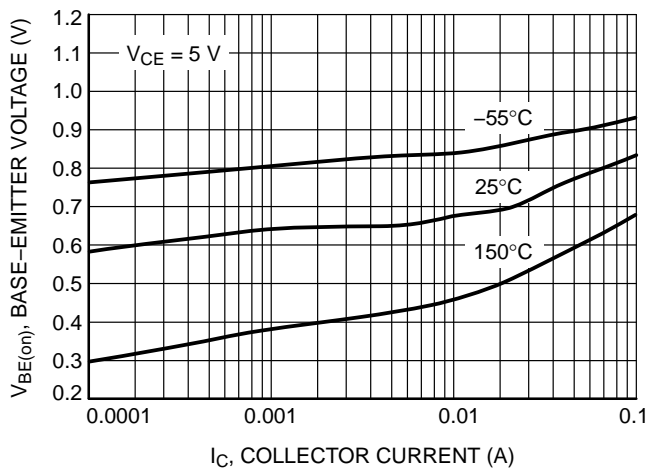


Figure 14. Base Emitter Voltage vs. Collector Current

BC846B

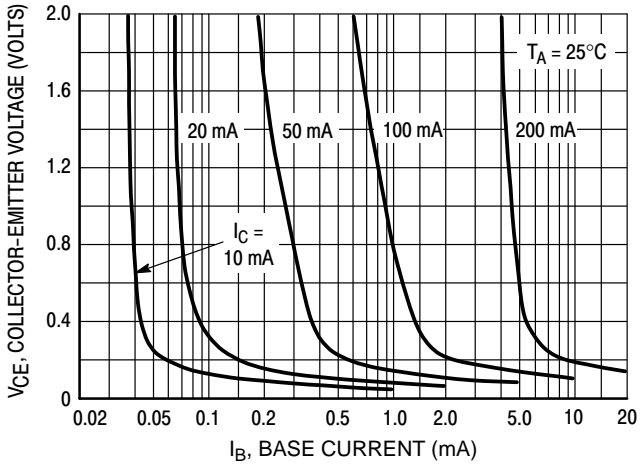


Figure 15. Collector Saturation Region

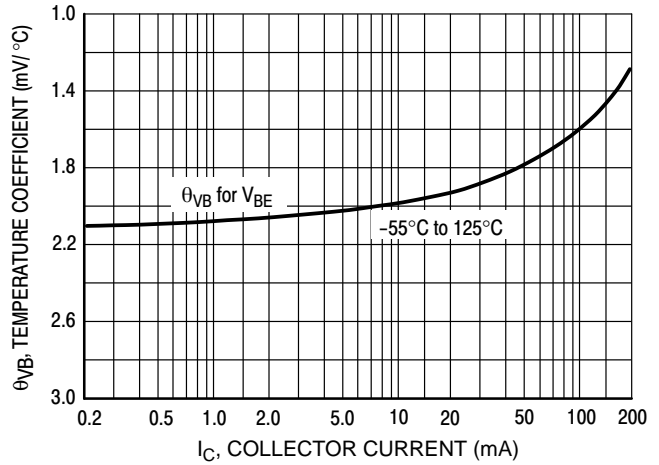


Figure 16. Base-Emitter Temperature Coefficient

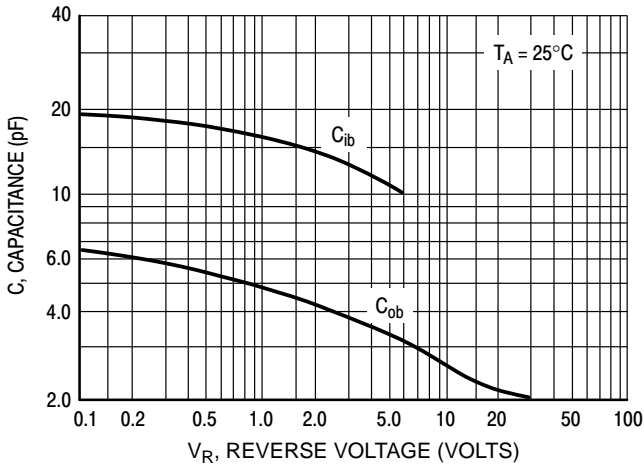


Figure 17. Capacitance

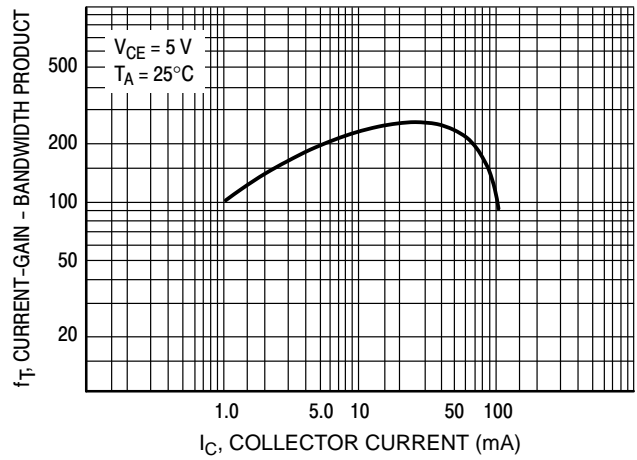


Figure 18. Current-Gain - Bandwidth Product

BC846, BC847, BC848

BC847B, BC848B

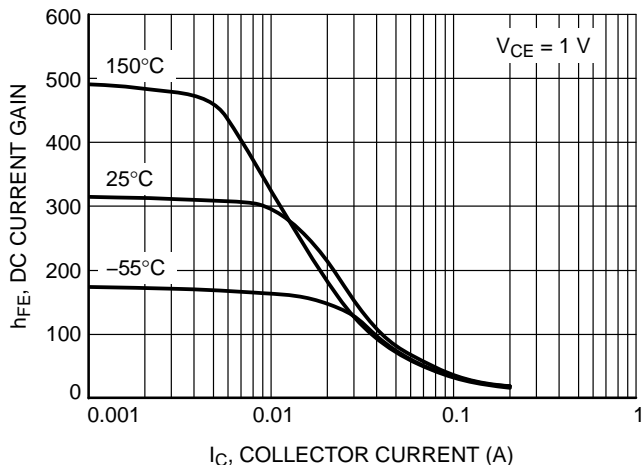


Figure 19. DC Current Gain vs. Collector Current

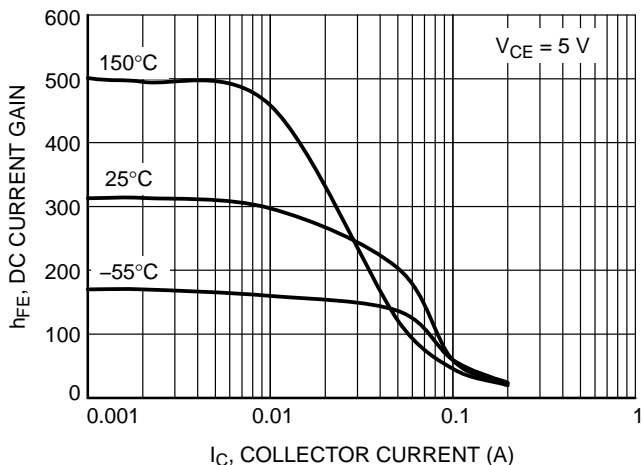


Figure 20. DC Current Gain vs. Collector Current

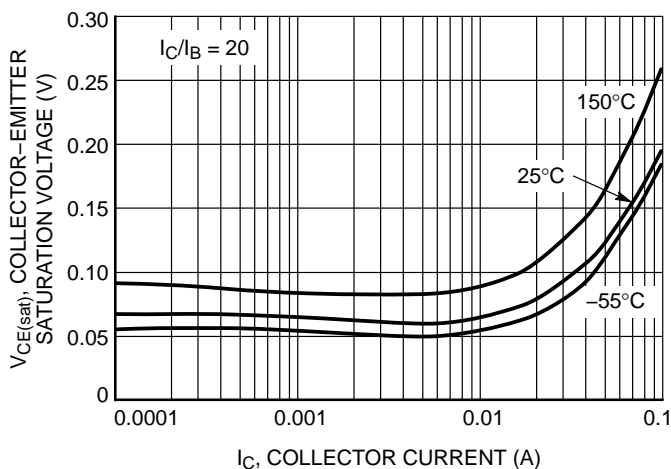


Figure 21. Collector Emitter Saturation Voltage vs. Collector Current

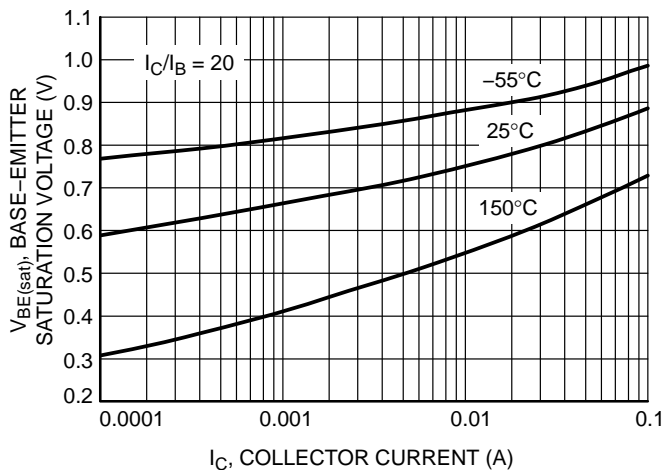


Figure 22. Base Emitter Saturation Voltage vs. Collector Current

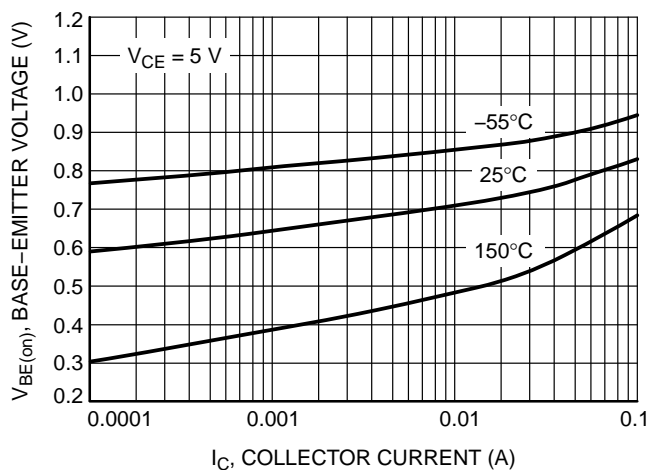


Figure 23. Base Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC847B, BC848B

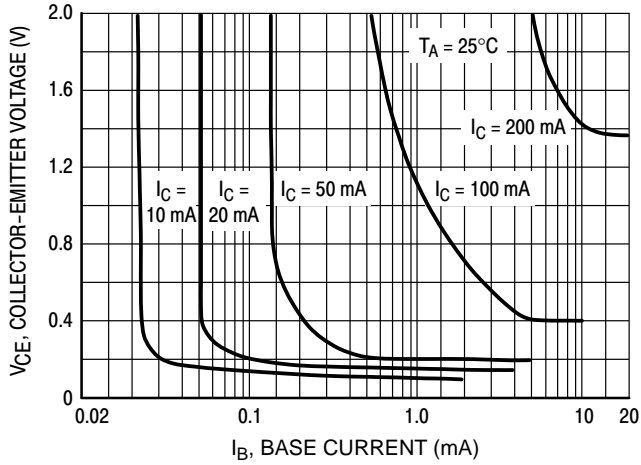


Figure 24. Collector Saturation Region

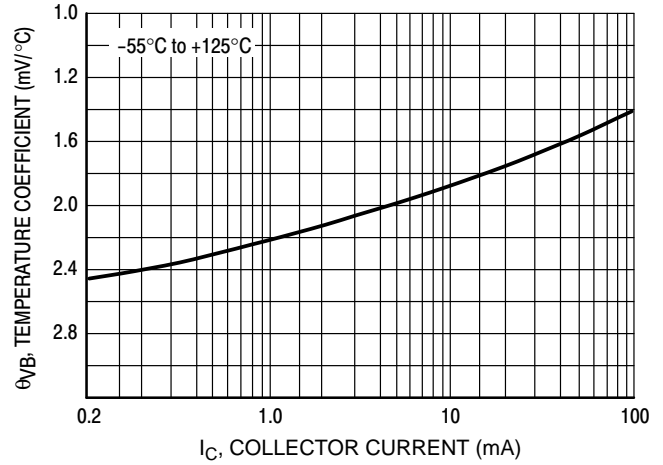


Figure 25. Base-Emitter Temperature Coefficient

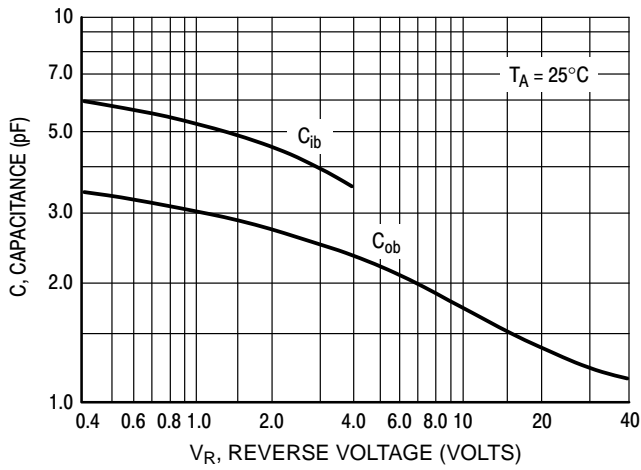


Figure 26. Capacitances

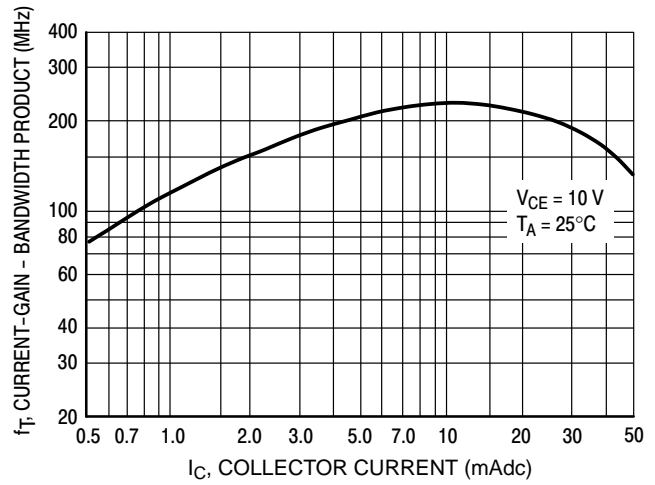


Figure 27. Current-Gain - Bandwidth Product

BC846, BC847, BC848

BC847C, BC848C

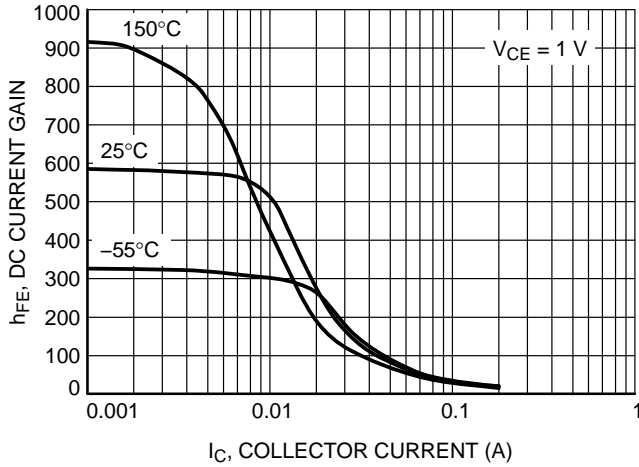


Figure 28. DC Current Gain vs. Collector Current

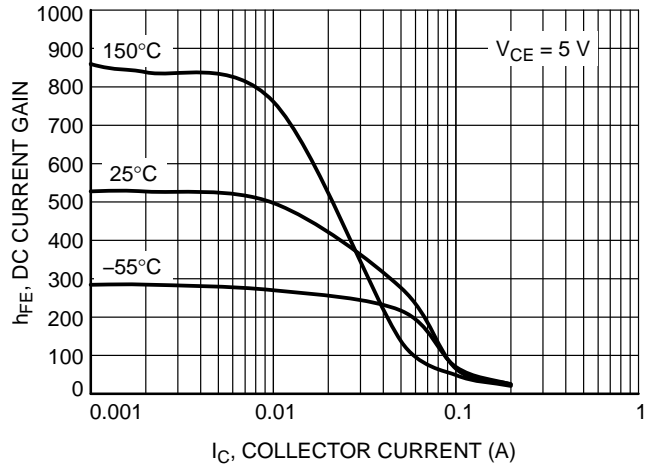


Figure 29. DC Current Gain vs. Collector Current

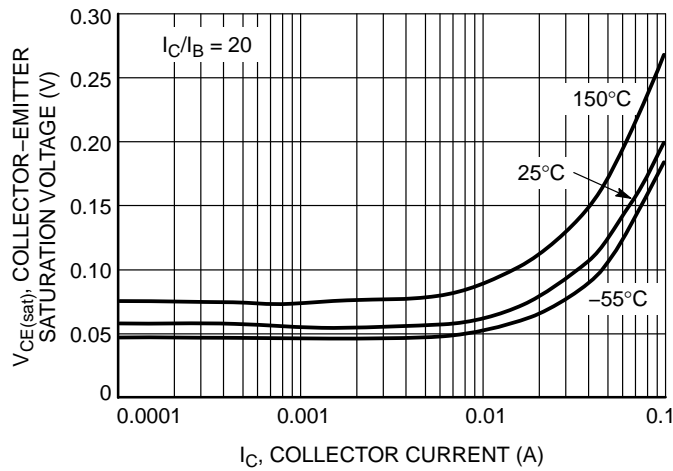


Figure 30. Collector Emitter Saturation Voltage vs. Collector Current

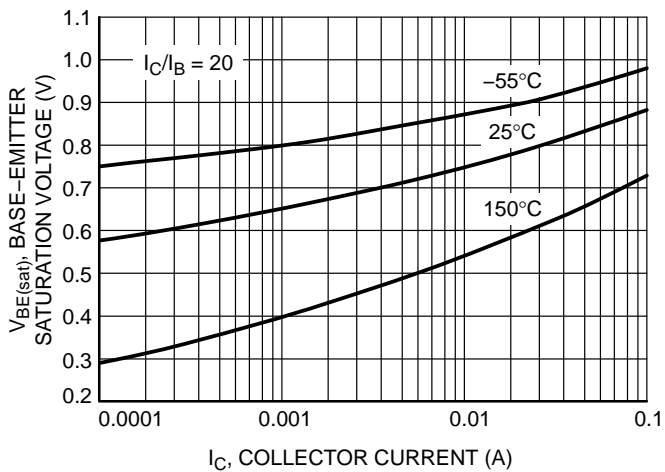


Figure 31. Base Emitter Saturation Voltage vs. Collector Current

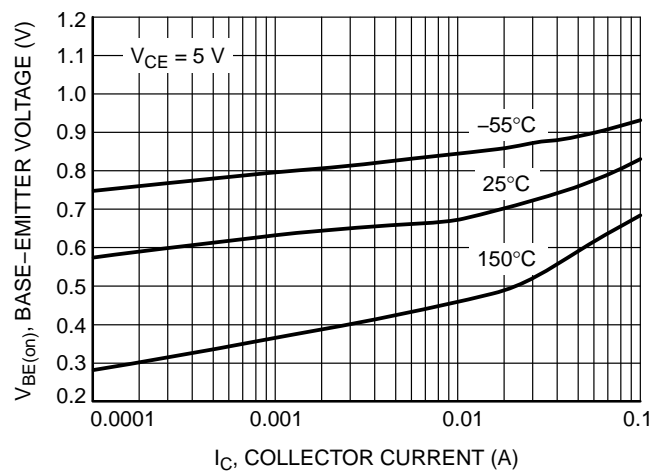


Figure 32. Base Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC847C, BC848C

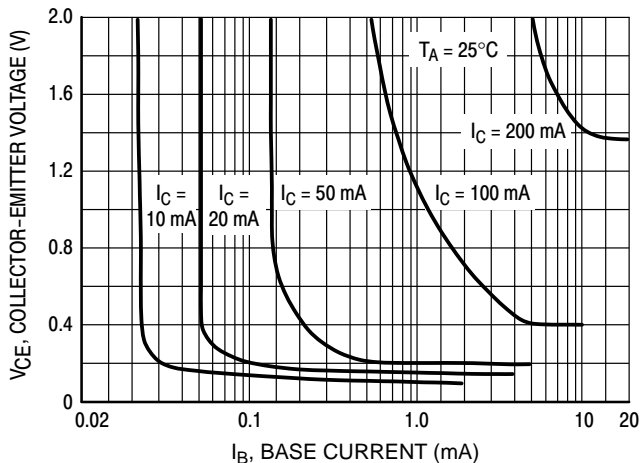


Figure 33. Collector Saturation Region

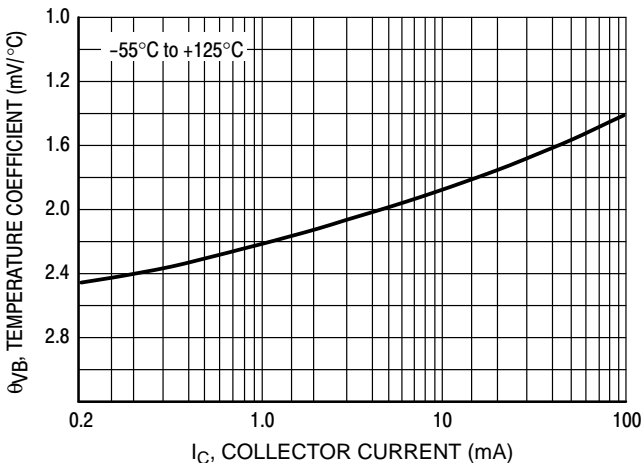


Figure 34. Base-Emitter Temperature Coefficient

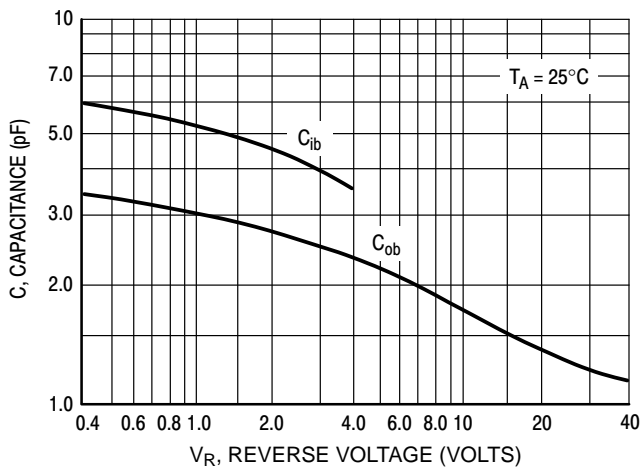


Figure 35. Capacitances

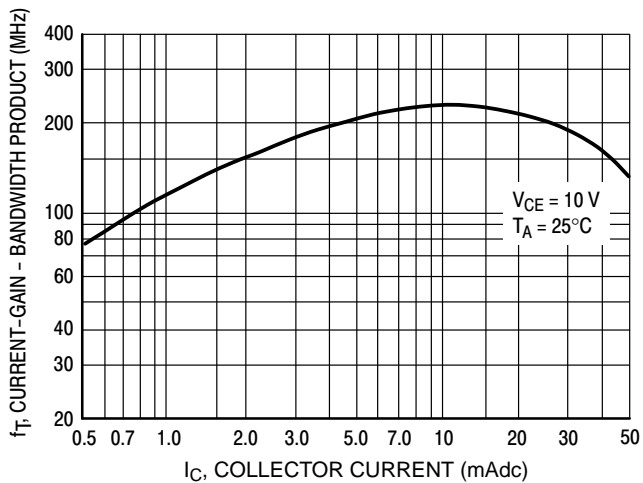


Figure 36. Current-Gain - Bandwidth Product

BC846, BC847, BC848

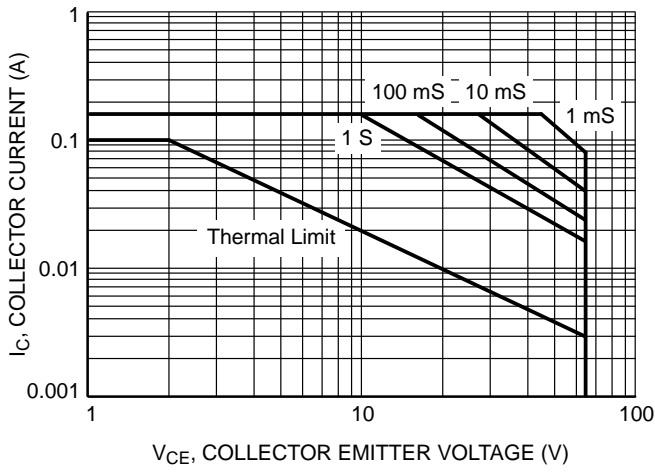


Figure 37. Safe Operating Area for BC846A, BC846B

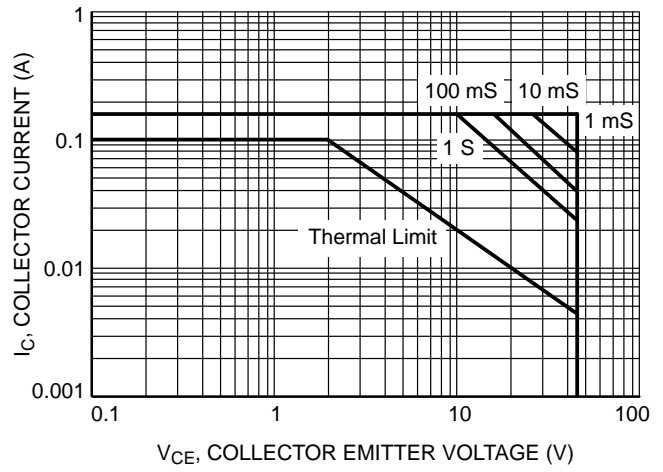


Figure 38. Safe Operating Area for BC847A, BC847B, BC847C

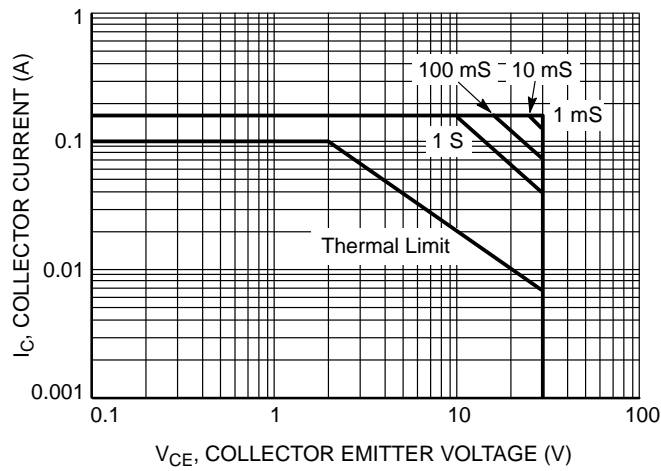


Figure 39. Safe Operating Area for BC848A, BC848B, BC848C

BC846, BC847, BC848

DEVICE ORDERING AND SPECIFIC MARKING INFORMATION

Device	Specific Marking Code	Package	Shipping†
BC846BWT1G	1B	SC-70 (SOT-323) (Pb-Free)	3,000 / Tape & Reel
SBC846BWT1G*			
BC847AWT1G	1E		3,000 / Tape & Reel
SBC847AWT1G*			
BC847BWT1G	1F		3,000 / Tape & Reel
SBC847BWT1G*			
BC847CWT1G	1G		3,000 / Tape & Reel
SBC847CWT1G*			
BC847CWT3G	1G		10,000 / Tape & Reel
SBC847CWT3G*			
BC848BWT1G	1K		3,000 / Tape & Reel
NSVBC848BWT1G*			
BC848CWT1G	1L		

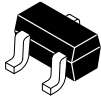
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

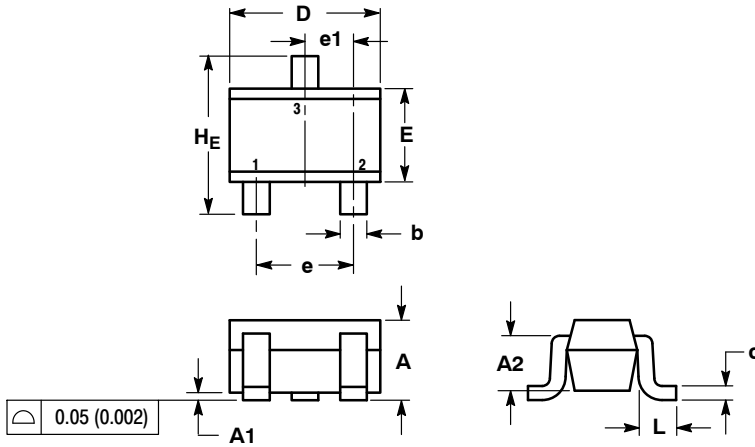
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SCALE 4:1

SC-70 (SOT-323)
CASE 419-04
ISSUE N

DATE 11 NOV 2008

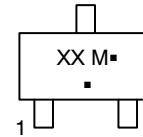


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

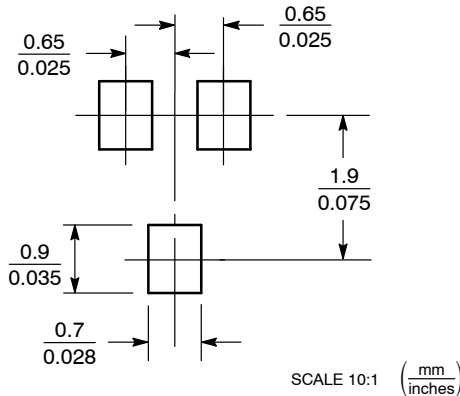
GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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